

CERTIFICATE OF TRANSMISSION BY FACSIMILE (37 CFR 1.8)Applicant(s): **Lanzerotti et al.**

Docket No.

BUR920010146US2

Application No.

10/660,048

Filing Date

09/11/03

Examiner

Unknown

Group Art Unit

2814Invention: **SILICON GERMANIUM HETEROJUNCTION BIPOLAR TRANSISTOR WITH CARBON INCORPORATION**

I hereby certify that this

Response to Notice of Non-Compliant Amendment*(Identify type of correspondence)*Is being facsimile transmitted to the United States Patent and Trademark Office (Fax. No. **703-872-9306**)

on

12/16/04*(Date)***Frederick W. Gibb, III***(Typed or Printed Name of Person Signing Certificate)**(Signature)*

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In re patent application of

Lanzerotti et al.

Serial No.: 10/660,048

Group Art Unit: 2814

Filed: September 11, 2003

Examiner: Unknown

For: SILICON GERMANIUM HETEROJUNCTION BIPOLAR
TRANSISTOR WITH CARBON INCORPORATIONCommissioner For Patents
P.O. Box 1450
Alexandria, VA 22313-1450**RESPONSE TO NOTICE OF NON-COMPLIANT AMENDMENT**

Sir:

In response to the Notice of Non-Compliant Amendment dated 12/07/04, a complete listing of the claims is provided herewith.

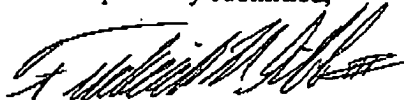
IN THE CLAIMS:

Claims 1-8 (Cancelled).

9. (Original) A semiconductor for use in a bipolar transistor, said semiconductor comprising:
carbon atoms; and
a dopant interacting with said carbon atoms,
wherein said carbon atoms limit outdiffusion of said dopant and said dopant is included in sufficient quantities to reduce a resistance of said semiconductor to less than approximately 4 Kohms/cm².

Please charge any deficiencies in fees and credit any overpayment of fees to
Attorney's Deposit Account No. 09-0456.

Respectfully submitted,



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